

Praneeth Ranga

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Effect of extended defects on photoluminescence of gallium oxide and aluminum gallium oxide epitaxial films. Scientific Reports, 2022, 12, 3243.	1.6	16
2	4.4 kV \hat{I}^2 -Ga ₂ O ₃ MESFETs with power figure of merit exceeding 100 MW cm ⁻² . Applied Physics Express, 2022, 15, 061001.	1.1	40
3	Plasmon-Phonon Coupling in Electrostatically Gated \hat{I}^2 -Ga ₂ O ₃ Films with Mobility Exceeding 200 cm ² V ⁻¹ s ⁻¹ . ACS Nano, 2022, 16, 8812-8819. ^{7.3}		8
4	Lateral Gallium Oxide Field Effect Transistors with High Figure of Merit. , 2022, , .		0
5	Oxygen annealing induced changes in defects within \hat{I}^2 -Ga ₂ O ₃ epitaxial films measured using photoluminescence. Journal Physics D: Applied Physics, 2021, 54, 174004.	1.3	11
6	Impurity band conduction in Si-doped \hat{I}^2 -Ga ₂ O ₃ films. Applied Physics Letters, 2021, 118, .	1.5	11
7	Optical Characterization of Gallium Oxide \hat{I}^2 and \hat{I}^2 Polymorph Thin-Films Grown on c-Plane Sapphire. Journal of Electronic Materials, 2021, 50, 2990-2998.	1.0	9
8	N-type doping of low-pressure chemical vapor deposition grown \hat{I}^2 -Ga ₂ O ₃ thin films using solid-source germanium. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	14
9	130Åm ² \hat{I}^2 -Ga ₂ O ₃ metal semiconductor field effect transistor with low-temperature metalorganic vapor phase epitaxy-regrown ohmic contacts. Applied Physics Express, 2021, 14, 076502.	1.1	39
10	In Situ Dielectric Al ₂ O ₃ / \hat{I}^2 -Ga ₂ O ₃ Interfaces Grown Using Metal-Organic Chemical Vapor Deposition. Advanced Electronic Materials, 2021, 7, 2100333.	2.6	17
11	High-k Oxide Field-Plated Vertical (001) \hat{I}^2 -Ga ₂ O ₃ Schottky Barrier Diode With Baliga TM s Figure of Merit Over 1 GW/cm ² . IEEE Electron Device Letters, 2021, 42, 1140-1143.	2.2	86
12	Thermal Conductivity of \hat{I}^2 -Phase Ga ₂ O ₃ and (Al _x Ga _{1-x}) ₂ O ₃ /Ga ₂ O ₃ Heteroepitaxial Thin Films. ACS Applied Materials & Interfaces, 2021, 13, 38477-38490.		24
13	Multi-kV Class \hat{I}^2 -Ga ₂ O ₃ MESFETs With a Lateral Figure of Merit Up to 355 MW/cm ² . IEEE Electron Device Letters, 2021, 42, 1272-1275.	2.2	50
14	Growth and characterization of metalorganic vapor-phase epitaxy-grown \hat{I}^2 -(Al _x Ga _{1-x}) ₂ O ₃ /Ga ₂ O ₃ modulation doped field effect transistors. Applied Physics Express, 2021, 14, 025501.	1.1	40
15	Electro-thermal co-design of \hat{I}^2 -(Al _x Ga _{1-x}) ₂ O ₃ /Ga ₂ O ₃ modulation doped field effect transistors. Applied Physics Letters, 2020, 117, .	1.5	35
16	Low temperature homoepitaxy of (010) \hat{I}^2 -Ga ₂ O ₃ by metalorganic vapor phase epitaxy: Expanding the growth window. Applied Physics Letters, 2020, 117, .	1.5	56
17	Compensation in (2 \hat{I}^2) homoepitaxial \hat{I}^2 -Ga ₂ O ₃ thin films grown by metalorganic vapor-phase epitaxy. Journal of Applied Physics, 2020, 128, .	1.1	13
18	Delta-doped \hat{I}^2 -Ga ₂ O ₃ films with narrow FWHM grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2020, 117, .	1.5	17

#	ARTICLE	IF	CITATIONS
19	Highly tunable, polarization-engineered two-dimensional electron gas in $\text{InAlGaO}_3/\text{InGaO}_3$ heterostructures. Applied Physics Express, 2020, 13, 061009.	1.1	38
20	Delta-doped InGaO_3 thin films and $\text{In}-(\text{Al}_{0.26}\text{Ga}_{0.74})_2\text{O}_3/\text{InGaO}_3$ heterostructures grown by metalorganic vapor-phase epitaxy. Applied Physics Express, 2020, 13, 045501.		38
21	Schottky Barrier Height Engineering in InGaO_3 Using SiO_2 Interlayer Dielectric. IEEE Journal of the Electron Devices Society, 2020, 8, 286-294.	1.2	32
22	The anisotropic quasi-static permittivity of single-crystal InGaO_3 measured by terahertz spectroscopy. Applied Physics Letters, 2020, 117, .	1.5	27
23	Si-doped $\text{In}-(\text{Al}_{0.26}\text{Ga}_{0.74})_2\text{O}_3$ thin films and heterostructures grown by metalorganic vapor-phase epitaxy. Applied Physics Express, 2019, 12, 111004.	1.1	47